

Search History 1/9/05 (2pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8	(US-20040195621-\$ or US-20030107103-\$ or US-20030001196-\$ or US-20030006463-\$).did. or (US-6611027-\$ or US-6504213-\$ or US-6787410-\$ or US-6091630-\$). did.	US-PGPUB; USPAT	OR	OFF	2005/01/09 23:52
L2	2991	((257/355) or (257/368) or (257/446) or (257/501) or (257/506)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/01/09 23:52
L3	9	2 and drain near6 (separated separating separate spaced apart) near6 (sti shallow adj trench adj isolation trench adj isolation trench) and (leakage leaking leak)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 23:54
S1	5	"423065".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 20:28
S2	2	(("6504213") or ("6611027")).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/09 20:30
S3	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 20:42
S4	267	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:06
S5	33	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3) and trap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 20:43
S6	13	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3) and plan adj view and gate near6 length	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 20:51
S7	3027	leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:06

S8	247	trap and leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:07
S9	234	(trap and leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)) not S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:07
S10	7	(US-20040195621-\$ or US-20030107103-\$ or US-20030001196-\$).did. or (US-6611027-\$ or US-6504213-\$ or US-6787410-\$ or US-6091630-\$). did.	US-PGPUB; USPAT	OR	OFF	2005/01/09 21:39
S11	0	(2003/0006463).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:39
S12	2	("20030006463").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:41
S13	2	jp-2001204272\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 22:10
S14	24	drain adj2 region near10 (separated apart spaced-apart) near10 (isolation adj structure sti shallow adj trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 22:11

10/647604

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READY FOR EXAMINATION

- READING FOR EXAMINATION

TRANSITION

Continuity/Foreign Data report

GAU: 2826

GALL: 2026

GADU. 2020

Patent Number: Issue Date: N/A
Title: ULTRA LOW LEAKAGE MOSFET TRANSISTOR

No foreign data for this application.

No parent data for this application.

No child data for this application.

Patent No.: 01/09/2005